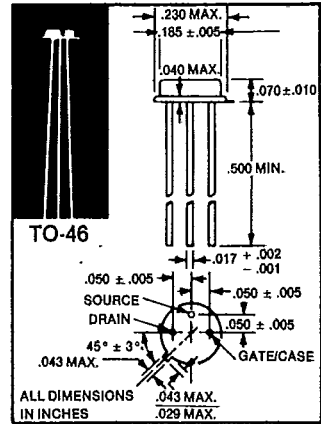


POWRFET™
SILICON EPITAXIAL JUNCTION
N-CHANNEL FIELD EFFECT TRANSISTOR

CP643

GEOMETRY 446

- FOR HIGH DYNAMIC RANGE R.F. AMPLIFIERS
- SPECIFIED FOR H.F. BAND – USEABLE THRU 500 MHz
- LOW NOISE FIGURE DIRECT FROM 50 Ohm LINE²



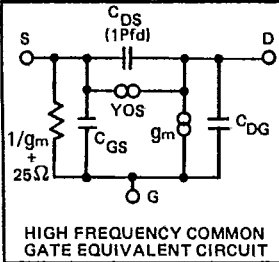
TYPICAL CHARACTERISTICS
IN CIRCUIT OF TMF 18

Dynamic Range 140 dB
Two Tone @ 3 MHz/5MHz
3rd Order Prod.

Signal Level	Typ. 3rd Order Product
0.25 Volt (OdBm)	- 68dB

ELECTRICAL DATA ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL		UNITS
Drain to Source Voltage	BV _{DSO}	30	Volts
Drain to Gate Voltage	BV _{DGO}	30	Volts
Gate to Source Voltage	BV _{GSO}	-15	Volts
Peak Drain Current	I _D	0.3	Amps
Power Dissipation 25°C CASE	P _D	2.0	Watts
Derating Factor (slope)	DF	87	°C/W
Junction Temp. (Oper. & Store)	T _J	-55°C to +200°C	

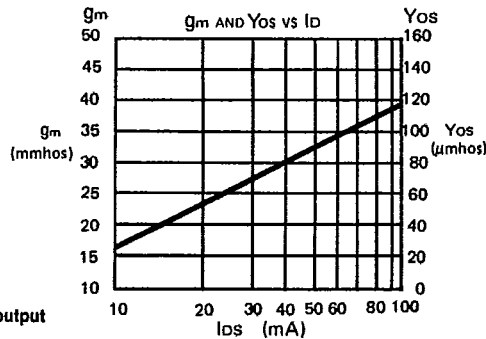
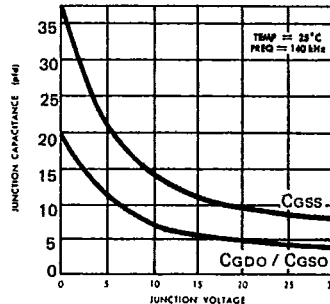


ELECTRICAL CHARACTERISTICS: T_{case} = 25°C (UNLESS OTHERWISE STATED)

PARAMETERS AND CONDITIONS	SYMBOL	CP 643			UNITS
		Min.	Typ.	Max.	
Gate Leakage Current V _{GS} = -15V, V _{DS} = 0	I _{GSS}	-	1.0	10	nA
Gate Leakage Current V _{GS} = -15V, V _{DS} = 0, T _C = 125°C	I _{GSS}	-	-	10	μA
Transconductance V _{DS} = 15V, I _{DS} = 25 mA	g _m	20	25	30	mMhos
Pinch-Off Voltage V _{DS} = 5V, I _{DS} = 1.0 mA	V _{PO}	2.0	4.0	7.0	Volts
Gain in Ckt. of TMF18 I _{DS} = 25 mA, f = 1 to 100 MHz.	A	8.0	9.0	10.0	dB
Gate to Source Cap. V _{GS} = -20V	C _{GS}	-	5	6	pf
Gate to Drain Cap. V _{GD} = -20V	C _{GD}	-	5	6	pf
Drain Current ¹ V _{DS} = 15V, V _{GS} = 0	I _{DSS}	50	100	250	mAmps
TMF18 ² I _{DS} = 25 mA, f = 1 MHz.	N.F.	-	4.0	5.0	dB

¹Pulse Measurement 1% Duty Cycle 10 mS Max.
²The noise figure will be improved at the cost of gain when used in a 75Ω line with a 2:1 output winding ratio or in a 50Ω line with an input step up transformer.
³The gain may be raised at a sacrifice in bandwidth by increasing the output transformer ratio.

JUNCTION CAPACITANCE VS VOLTAGE



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